

**Features :**

- Isolated mounting base 2500V~
- Pressure contact technology with Increased power cycling capability
- Space and weight saving

**Typical Applications**

- Inverter
- Inductive heating
- Chopper

$V_{DSM}, V_{RSM}$	$V_{DRM}, V_{RRM}$	品名
2100V	2000V	Mx70TF200
2300V	2200V	Mx70TF220
2600V	2500V	Mx70TF250

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	$T_j(^\circ C)$	VALUE			UNIT
				Min.	Typ.	Max.	
$I_{T(AV)}$	Mean on-state current	180° half sine wave 50Hz Single side cooled, $T_c=85^\circ C$	125			70	A
$I_{T(RMS)}$	RMS on-state current					110	A
$I_{DRM}$ $I_{RRM}$	Repetitive peak current	at $V_{DRM}$ at $V_{RRM}$	125			30	mA
$I_{TSM}$	Surge on-state current	10ms half sine wave $V_R=60\%V_{RRM}$	125			1.40	kA
$I^2t$	$I^2t$ for fusing coordination					9.80	$A^2s \times 10^3$
$V_{TO}$	Threshold voltage		125			1.50	V
$r_T$	On-state slope resistance					4.90	$m\Omega$
$V_{TM}$	Peak on-state voltage	$I_{TM}=300A$	25			3.20	V
$dv/dt$	Critical rate of rise of off-state voltage	$V_{DM}=67\%V_{DRM}$	125			800	$V/\mu s$
$di/dt$	Critical rate of rise of on-state current	Gate source 1.5A $t_r \leq 0.5\mu s$ Repetitive	125			200	$A/\mu s$
$t_q$	Circuit commutated turn-off time	$I_{TM}=200A, t_p=2000\mu s, V_R=50V$ $dv/dt=30V/\mu s, di/dt=-20A/\mu s$	125	20		40	$\mu s$
$t_{rr}$	Reverse recovery time	$I_{TM}=200A, t_p=2000\mu s,$ $-di/dt=20A/\mu s, V_R=50V$	125		2		$\mu s$
$I_{GT}$	Gate trigger current	$V_A=12V, I_A=1A$	25	30		180	mA
$V_{GT}$	Gate trigger voltage			1.0		3.0	V
$I_H$	Holding current			20		200	mA
$V_{GD}$	Non-trigger gate voltage	$V_{DM}=67\%V_{DRM}$	125	0.2			V
$R_{th(j-c)}$	Thermal resistance Junction to case	D.C. Single side cooled per chip				0.230	$^\circ C/W$
$R_{th(c-h)}$	Thermal resistance case to heatsink	D.C. Single side cooled per chip				0.040	$^\circ C/W$
$V_{iso}$	Isolation voltage	50Hz,R.M.S,t=1min, $I_{iso}:1mA(MAX)$		3000			V
$F_m$	Terminal connection torque(M6)			3.5		5.0	$N\cdot m$
	Mounting torque(M6)				6.0		$N\cdot m$
$T_{vj}$	Junction temperature			-40		125	$^\circ C$
$T_{stg}$	Stored temperature			-40		125	$^\circ C$
$W_t$	Weight				320		g
Outline		M02					

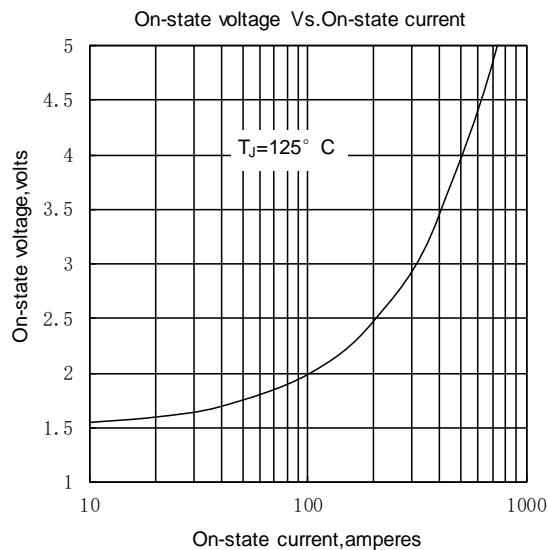


Fig.1  
Surge current Vs.Cycles

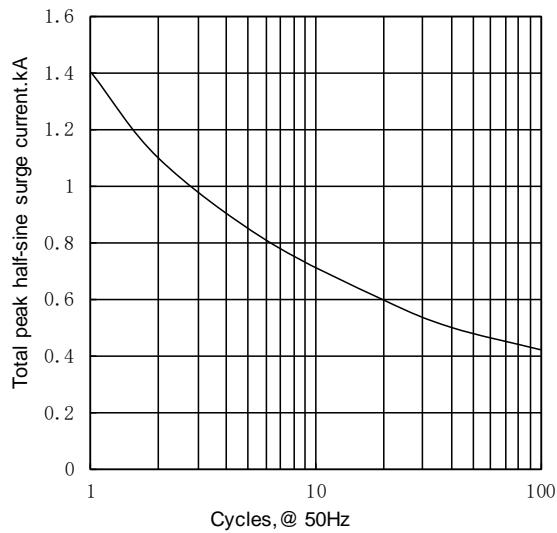


Fig.3

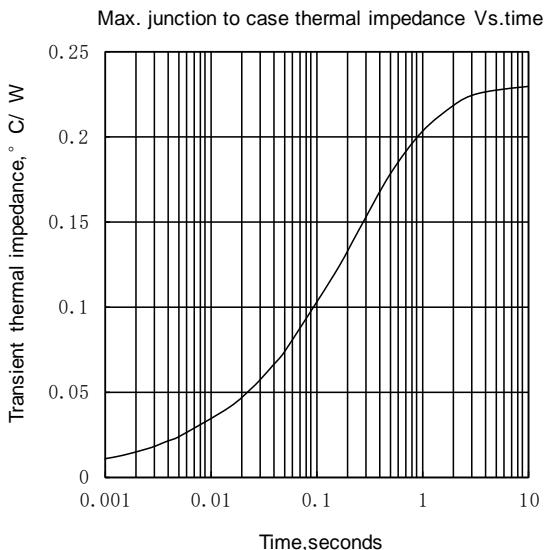


Fig.2  
Gate characteristic at 25° C junction temperature

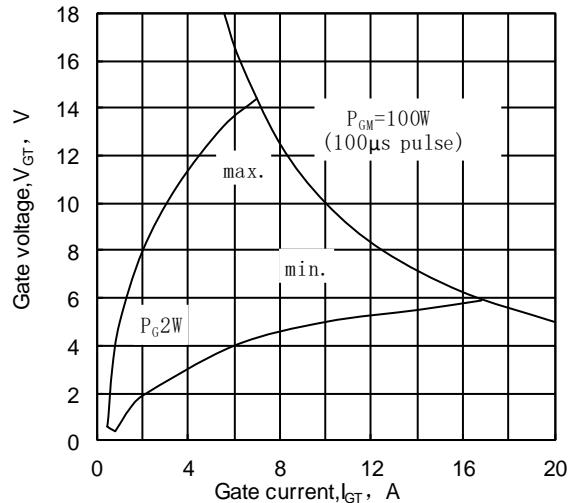


Fig.4

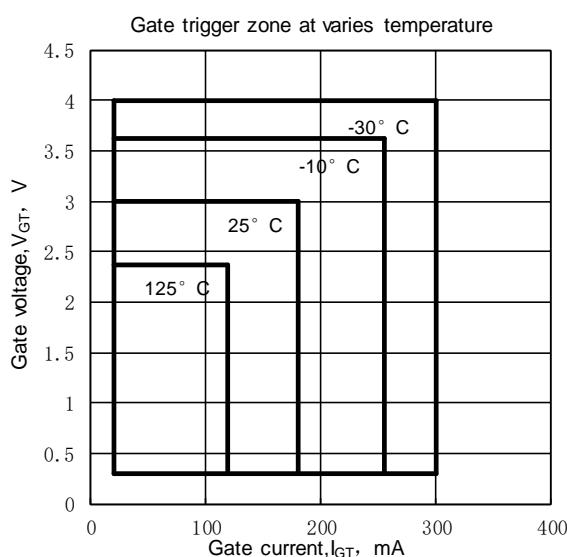
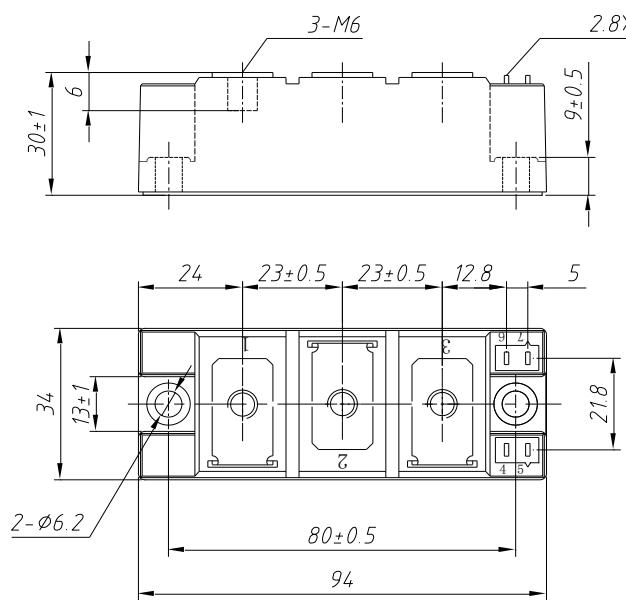


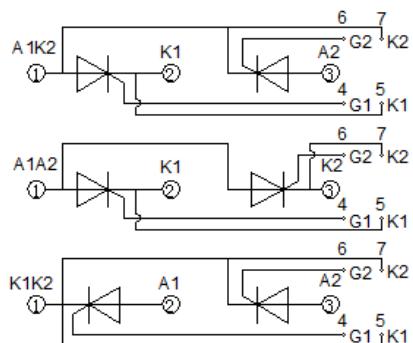
Fig.5



MD70TF\*\*

MR70TF\*\*

MC70TF\*\*

Unmarked dimensional tolerance :  $\pm 0.5\text{mm}$